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# 💫 National Semiconductor

## LM6161/LM6261/LM6361 High Speed Operational Amplifier

## **General Description**

The LM6161 family of high-speed amplifiers exhibits an excellent speed-power product in delivering 300 V/µs and 50 MHz unity gain stability with only 5 mA of supply current. Further power savings and application convenience are possible by taking advantage of the wide dynamic range in operating supply voltage which extends all the way down to +5V. These amplifiers are built with National's VIP<sup>TM</sup> (Vertically Integrated PNP) process which provides fast PNP transistors that are true complements to the already fast NPN devices. This advanced junction-isolated process delivers high speed performance without the need for complex and expensive dielectric isolation.

#### Features

■ High slew rate 300 V/µs

## **Connection Diagrams**

	Flatpak	Ad 8 0 1 V Ad		57-5
	Temperature Range		Package	NSC
Military	Industrial	Commercial		Drawing
	–25°C ≤ T₄ ≤ +85°C			
–55°C ≤ $T_A$ ≤ +125°C		$0^{\circ}C \leq T_{A} \leq +70^{\circ}C$		
$-55 \text{ C} \le \text{I}_{\text{A}} \le +125 \text{ C}$	LM6261N	0°C ≤ 1 <sub>A</sub> ≤ +70°C LM6361N	8-Pin	N08E
-55 C ≤ I <sub>A</sub> ≤ +125 C	A		8-Pin Molded DIP	N08E
	A		-	N08E J08A
LM6161J/883	A	LM6361N	Molded DIP	
LM6161J/883	A	LM6361N	Molded DIP 8-Pin	
LM6161J/883	LM6261N	LM6361N LM6361J	Molded DIP 8-Pin Ceramic DIP	J08A
LM6161J/883 5962-8962101PA	LM6261N	LM6361N LM6361J	Molded DIP 8-Pin Ceramic DIP 8-Pin Molded	J08A M08A
LM6161J/883 5962-8962101PA LM6161WG/883	LM6261N	LM6361N LM6361J	Molded DIP 8-Pin Ceramic DIP 8-Pin Molded Surface Mt.	J08A M08A
-55 C ≤ T <sub>A</sub> ≤ +125 C LM6161J/883 5962-8962101PA LM6161WG/883 5962-8962101XA LM6161W/883	LM6261N	LM6361N LM6361J	Molded DIP 8-Pin Ceramic DIP 8-Pin Molded Surface Mt. 10-Lead	J08A

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#### High unity gain freq 50 MHz

- Low supply current 5 mA
- Fast settling 120 ns to 0.1%
- Low differential gain <0.1%
- Low differential phase 0.1°
- Wide supply range 4.75V to 32V
- Stable with unlimited capacitive load
- Well behaved; easy to apply

## **Applications**

- Video amplifier
- High-frequency filter
- Wide-bandwidth signal conditioning
- Radar
- Sonar

## Absolute Maximum Ratings (Note 12)

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If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage (V <sup>+</sup> – V <sup>-</sup> )	36V
Differential Input Voltage	
(Note 8)	±8V
Common-Mode Voltage Range	
(Note 10)	$(V^+ - 0.7V)$ to $(V^- + 0.7V)$
Output Short Circuit to GND	
(Note 1)	Continuous
Soldering Information	Continuous
	Continuous 260°C
Soldering Information Dual-In-Line Package (N, J)	

See AN-450 "Surface Mounting Methods and Their Effect on Product Reliability" for other methods of soldering surface mount devices. Storage Temp Range -65°C to +150°C Max Junction Temperature 150°C

Max Junction Temperature150°CESD Tolerance (Notes 6, 7)±700V

## **Operating Ratings** (Note 12)

Temperature Range (Note 2)	
LM6161	$-55^{\circ}C \le T_{J} \le +125^{\circ}C$
LM6261	$-25^{\circ}C \le T_{J} \le +85^{\circ}C$
LM6361	$0^{\circ}C \le T_{J} \le +70^{\circ}C$
Supply Voltage Range	4.75V to 32V

## **DC Electrical Characteristics**

The following specifications apply for Supply Voltage =  $\pm 15V$ ,  $V_{CM} = 0$ ,  $R_L \ge 100 \text{ k}\Omega$  and  $R_S = 50\Omega$  unless otherwise noted. **Boldface** limits apply for  $T_J = T_{MIN}$  to  $T_{MAX}$ ; all other limits  $T_J = 25^{\circ}C$ .

Symbol	Parameter	Conditions	Тур	LM6161	LM6261	LM6361	Units
				Limit	Limit	Limit	1
				(Notes 3, 11)	(Note 3)	(Note 3)	
Vos	Input Offset Voltage		5	7	7	20	mV
				10	9	22	Max
Vos	Input Offset Voltage		10				µV/°C
Drift	Average Drift						
I <sub>b</sub>	Input Bias Current		2	3	3	5	μΑ
				6	5	6	Max
l <sub>os</sub>	Input Offset Current		150	350	350	1500	nA
				800	600	1900	Max
l <sub>os</sub>	Input Offset Current		0.4				nA/°C
Drift	Average Drift						
R <sub>IN</sub>	Input Resistance	Differential	325				kΩ
CIN	Input Capacitance	A <sub>V</sub> = +1 @ 10 MHz	1.5				pF
A <sub>VOL</sub>	Large Signal	$V_{OUT} = \pm 10V,$	750	550	550	400	V/V
	Voltage Gain	$R_L = 2 k\Omega$ (Note 9)		300	400	350	Min
		R <sub>L</sub> = 10 kΩ (Note 9)	2900				V/V
V <sub>CM</sub>	Input Common-Mode	Supply = $\pm 15V$	+14.0	+13.9	+13.9	+13.8	Volts
	Voltage Range			+13.8	+13.8	+13.7	Min
			-13.2	-12.9	-12.9	-12.8	Volts
				-12.7	-12.7	-12.7	Min
		Supply = +5V	4.0	3.9	3.9	3.8	Volts
		(Note 4)		3.8	3.8	3.7	Min
			1.8	2.0	2.0	2.1	Volts
				2.2	2.2	2.2	Max
CMRR	Common-Mode	$-10V \le V_{CM} \le +10V$	94	80	80	72	dB
	Rejection Ratio			74	76	70	Min
PSRR	Power Supply	$\pm 10V \le V^{\pm} \le \pm 16V$	90	80	80	72	dB
	Rejection Ratio			74	76	70	Min

## DC Electrical Characteristics (Continued)

The following specifications apply for Supply Voltage =  $\pm 15V$ ,  $V_{CM} = 0$ ,  $R_L \ge 100 \text{ k}\Omega$  and  $R_S = 50\Omega$  unless otherwise noted. **Boldface** limits apply for  $T_L = T_{MIN}$  to  $T_{MAX}$ ; all other limits  $T_L = 25^{\circ}C$ .

Symbol	Parameter	Conditions	Тур	LM6161	LM6261 Limit	LM6361	Units
				Limit		Limit	1
				(Notes 3, 11)	(Note 3)	(Note 3)	
Vo	Output Voltage	Supply = $\pm 15V$	+14.2	+13.5	+13.5	+13.4	Volts
	Swing	and $R_L = 2 k\Omega$		+13.3	+13.3	+13.3	Min
			-13.4	-13.0	-13.0	-12.9	Volts
				-12.7	-12.8	-12.8	Min
		Supply = +5V	4.2	3.5	3.5	3.4	Volts
		and $R_L = 2 k\Omega$		3.3	3.3	3.3	Min
		(Note 4)	1.3	1.7	1.7	1.8	Volts
				2.0	1.9	1.9	Max
	Output Short	Source	65	30	30	30	mA
	Circuit Current			20	25	25	Min
		Sink	65	30	30	30	mA
				20	25	25	Min
Is	Supply Current		5.0	6.5	6.5	6.8	mA
				6.8	6.7	6.9	Max

### **AC Electrical Characteristics**

The following specifications apply for Supply Voltage = ±15V,  $V_{CM}$  = 0,  $R_L \ge 100 \text{ k}\Omega$  and  $R_S$  = 50 $\Omega$  unless otherwise noted. Boldface limits apply for  $T_J$  =  $T_{MIN}$  to  $T_{MAX}$ ; all other limits  $T_J$  = 25°C.

				LM6161	LM6261	LM6361	
Symbol	Parameter	Conditions	Тур	Limit	Limit	Limit	Units
				(Notes 3, 11)	(Note 3)	(Note 3)	
GBW	Gain-Bandwidth	@ f = 20 MHz	50	40	40	35	MHz
	Product			30	35	32	Min
		Supply = $\pm 5V$	35				MHz
SR	Slew Rate	$A_{V} = +1$ (Note 8)	300	200	200	200	V/µs
				180	180	180	Min
		Supply = $\pm 5V$ (Note 8)	200				V/µs
PBW	Power Bandwidth	$V_{OUT} = 20 V_{PP}$	4.5				MHz
ts	Settling Time	10V Step to 0.1%	120				ns
		$A_V = -1, R_L = 2 k\Omega$					
φm	Phase Margin		45				Deg
A <sub>D</sub>	Differential Gain	NTSC, $A_V = +4$	<0.1				%
φD	Differential Phase	NTSC, $A_V = +4$	0.1				Deg
e <sub>np-p</sub>	Input Noise Voltage	f = 10 kHz	15				nV/√Hz
i <sub>np-p</sub>	Input Noise Current	f = 10 kHz	1.5				pA/√Hz

Note 1: Continuous short-circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C. Note 2: The typical junction-to-ambient thermal resistance of the molded plastic DIP (N) is 105°C/W, the molded plastic SO (M) package is 155°C/W, and the cerdip

(J) package is 125°C/W. All numbers apply for packages soldered directly into a printed circuit board.

Note 3: Limits are guaranteed by testing or correlation.

Note 4: For single supply operation, the following conditions apply:  $V^+ = 5V$ ,  $V^- = 0V$ ,  $V_{CM} = 2.5V$ ,  $V_{OUT} = 2.5V$ . Pin 1 & Pin 8 (Vos Adjust) are each connected to Pin 4 ( $V^-$ ) to realize maximum output swing. This connection will degrade  $V_{OS}$ ,  $V_{OS}$  Drift, and Input Voltage Noise.

Note 5:  $C_L \le 5 \text{ pF.}$ 

Note 6: In order to achieve optimum AC performance, the input stage was designed without protective clamps. Exceeding the maximum differential input voltage results in reverse breakdown of the base-emitter junction of one of the input transistors and probable degradation of the input parameters (especially Vos, los, and Noise).

## AC Electrical Characteristics (Continued)

Note 7: The average voltage that the weakest pin combinations (those involving Pin 2 or Pin 3) can withstand and still conform to the datasheet limits. The test circuit used consists of the human body model of 100 pF in series with 1500Ω.

Note 8:  $V_{IN}$  = 8V step. For supply = ±5V,  $V_{IN}$  = 5V step.

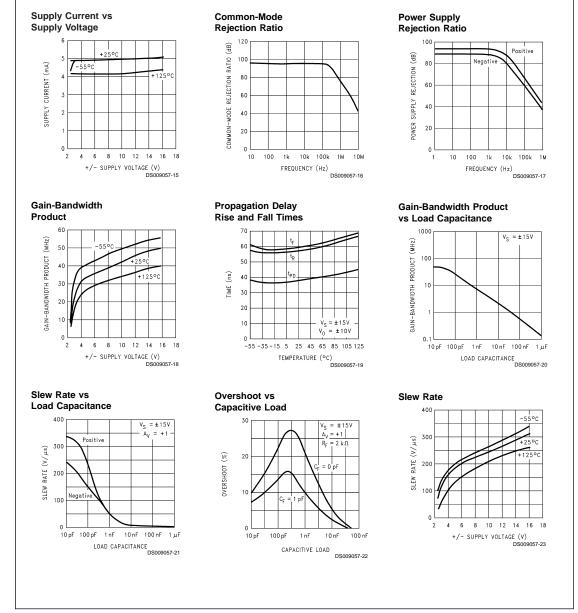
Note 9: Voltage Gain is the total output swing (20V) divided by the input signal required to produce that swing.

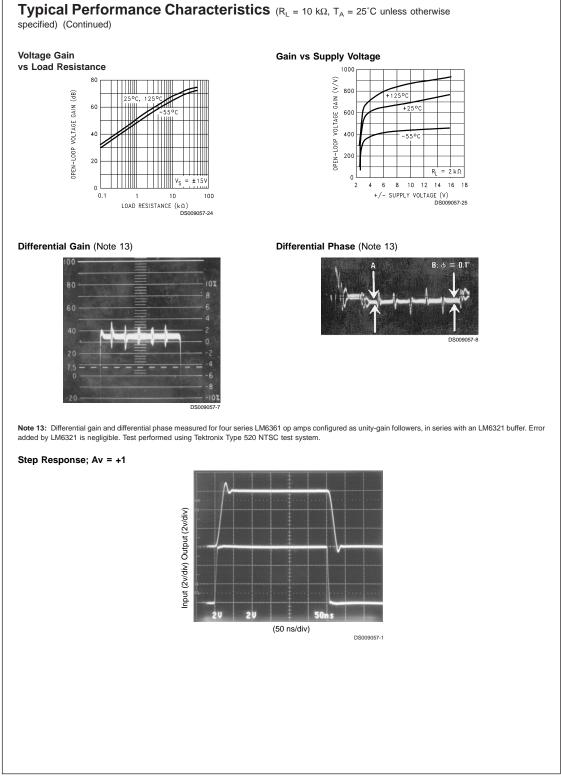
Note 10: The voltage between  $\mathsf{V}^{+}$  and either input pin must not exceed 36V.

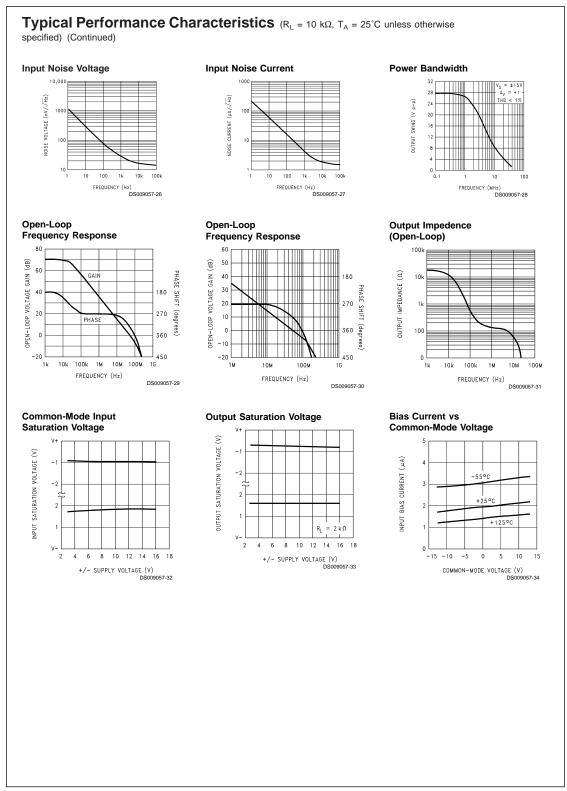
Note 11: A military RETS electrical test specification is available on request. At the time of printing, the RETS6161X specs complied with all Boldface limits in this column.

Note 12: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed.

## **Typical Performance Characteristics** ( $R_L = 10 \text{ k}\Omega$ , $T_A = 25^{\circ}C$ unless otherwise specified)

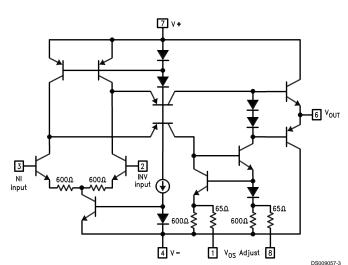






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#### **Simplified Schematic**



## **Applications Tips**

The LM6361 has been compensated for unity-gain operation. Since this compensation involved adding emitter-degeneration resistors to the op amp's input stage, the open-loop gain was reduced as the stability increased. Gain error due to reduced A<sub>VOL</sub> is most apparent at high gains; thus, for gains between 5 and 25, the less-compensated LM6364 should be used, and the uncompensated LM6365 is appropriate for gains of 25 or more. The LM6361, LM6364, and LM6365 have the same high slew rate, regardless of their compensation.

The LM6361 is unusually tolerant of capacitive loads. Most op amps tend to oscillate when their load capacitance is greater than about 200 pF (especially in low-gain circuits). The LM6361's compensation is effectively increased with load capacitance, reducing its bandwidth and increasing its stability.

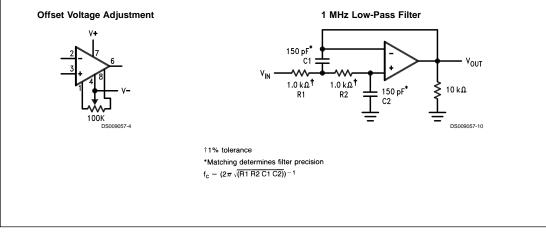
Power supply bypassing is not as critical for the LM6361 as it is for other op amps in its speed class. Bypassing will, how-

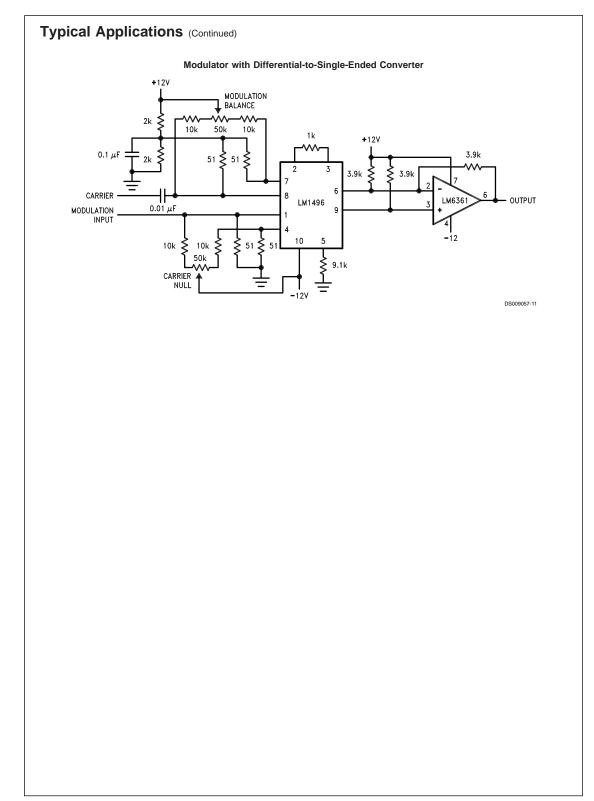
#### **Typical Applications**

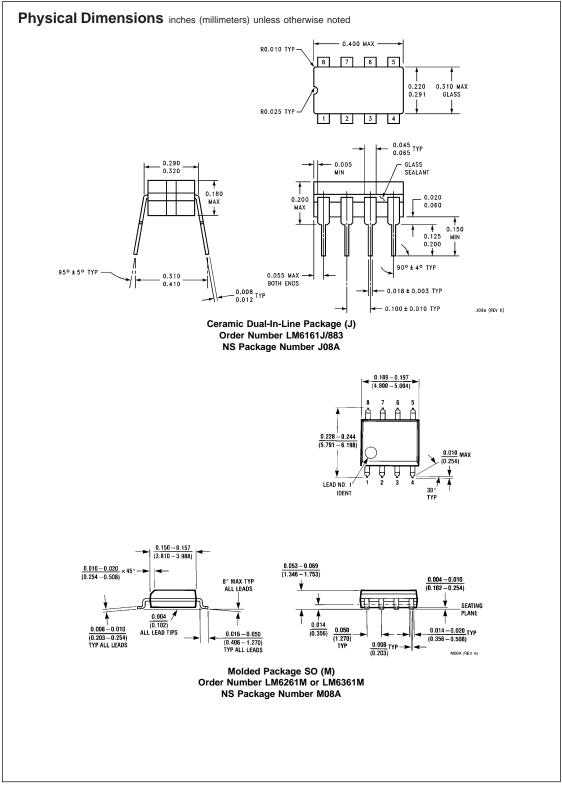
ever, improve the stability and transient response and is recommended for every design. 0.01  $\mu$ F to 0.1  $\mu$ F ceramic capacitors should be used (from each supply "rail" to ground); if the device is far away from its power supply source, an additional 2.2  $\mu$ F to 10  $\mu$ F of tantalum may provide extra noise reduction.

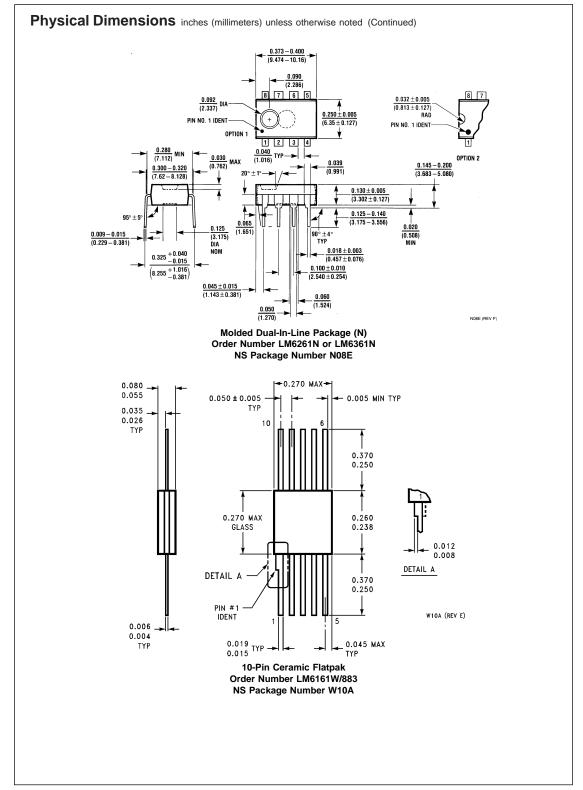
Keep all leads short to reduce stray capacitance and lead inductance, and make sure ground paths are low-impedance, especially where heavier currents will be flowing. Stray capacitance in the circuit layout can cause signal coupling across adjacent nodes and can cause gain to unintentionally vary with frequency.

Breadboarded circuits will work best if they are built using generic PC boards with a good ground plane. If the op amps are used with sockets, as opposed to being soldered into the circuit, the additional input capacitance may degrade circuit performance.









Notes

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